



5SDD 11T2800

Old part no. DV 827C-1100-28

Rectifier Diode

Properties

- Industry standard housing
- Suitable for parallel operation
- High operating temperature
- Low forward voltage drop

Key Parameters

V_{RRM}	=	2 800	V
I_{FAVm}	=	1 285	A
I_{FSM}	=	15 000	A
V_{TO}	=	0.933	V
r_T	=	0.242	mΩ

Types

	V_{RRM}
5SDD 11T2800	2 800 V
Conditions:	$T_j = -40 \div 160\text{ °C}$, half sine waveform, $f = 50\text{ Hz}$

Mechanical Data

F_m	Mounting force	$10 \pm 2\text{ kN}$
m	Weight	0.20 kg
D_s	Surface creepage distance	20 mm
D_a	Air strike distance	14 mm

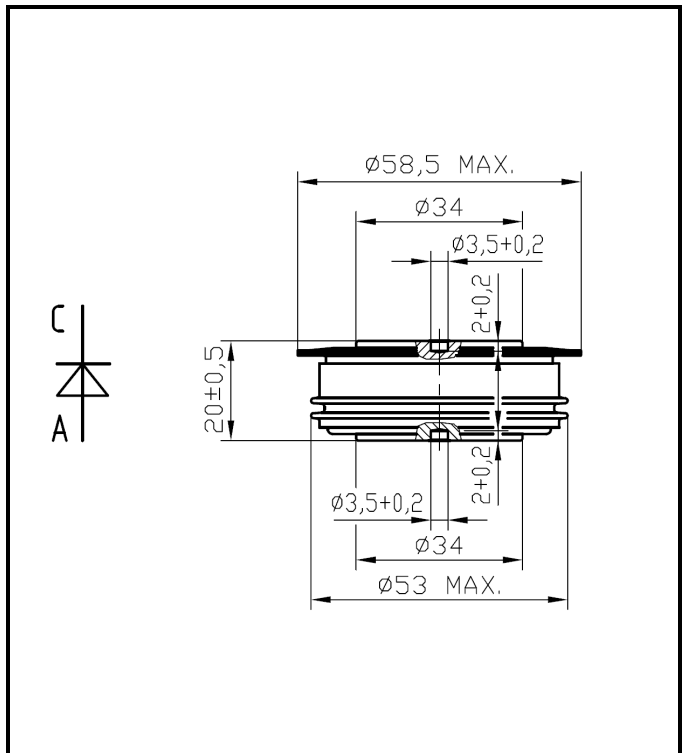


Fig. 1 Case



ABB s.r.o.

Novodvorska 1768/138a, 142 21 Praha 4, Czech Republic

tel.: +420 261 306 250, <http://www.abb.com/semiconductors>

Maximum Ratings			Maximum Limits	Unit
V_{RRM}	Repetitive peak reverse voltage $T_j = -40 \div 160\text{ }^{\circ}\text{C}$		2 800	V
I_{FAVM}	Average forward current $T_c = 85\text{ }^{\circ}\text{C}$		1 285	A
I_{FRMS}	RMS forward current $T_c = 85\text{ }^{\circ}\text{C}$		2 019	A
I_{RRM}	Repetitive reverse current $V_R = V_{RRM}$		30	mA
I_{FSM}	Non repetitive peak surge current $V_R = 0\text{ V, half sine pulse}$	$t_p = 8.3\text{ ms}$	16 000	A
		$t_p = 10\text{ ms}$	15 000	A
I^2t	Limiting load integral $V_R = 0\text{ V, half sine pulse}$	$t_p = 8.3\text{ ms}$	1 066 000	A ² s
		$t_p = 10\text{ ms}$	1 125 000	A ² s
$T_{jmin} - T_{jmax}$	Operating temperature range		-40 ÷ 160	°C
T_{STG}	Storage temperature range		-40 ÷ 160	°C

Unless otherwise specified $T_j = 160\text{ }^{\circ}\text{C}$

Characteristics		Value			Unit
		min	typ	max	
V_{T0}	Threshold voltage			0.933	V
r_T	Forward slope resistance $I_{F1} = 1\text{ 500 A, } I_{F2} = 4\text{ 500 A;}$			0.242	mΩ
V_{FM}	Maximum forward voltage $I_{FM} = 1\text{ 500 A}$			1.300	V
Q_{rr}	Recovered charge $V_R = 100\text{ V, } I_{FM} = 1\text{ 000 A, } di/dt = -30\text{ A/}\mu\text{s}$		2 200		μC

Unless otherwise specified $T_j = 160\text{ }^{\circ}\text{C}$

Thermal Parameters			Value	Unit
R_{thjc}	Thermal resistance junction to case	double side cooling	32	K/kW
		anode side cooling	50	
		cathode side cooling	88	
R_{thch}	Thermal resistance case to heatsink	double side cooling	8	K/kW
		single side cooling	16	

Transient Thermal Impedance

Analytical function for transient thermal impedance

$$Z_{thjc} = \sum_{i=1}^5 R_i (1 - \exp(-t / \tau_i))$$

Conditions:

$F_m = 10 \pm 2$ kN, Double side cooled

Correction for periodic waveforms

180° sine:	2.3 K/kW
180° rectangular:	3.1 K/kW
120° rectangular:	5.1 K/kW
60° rectangular:	8.7 K/kW

i	1	2	3	4	5
τ_i (s)	0.7033	0.2185	0.0588	0.0042	0.0006
R_i (K/kW)	11.56	10.08	7.84	2.38	0.13

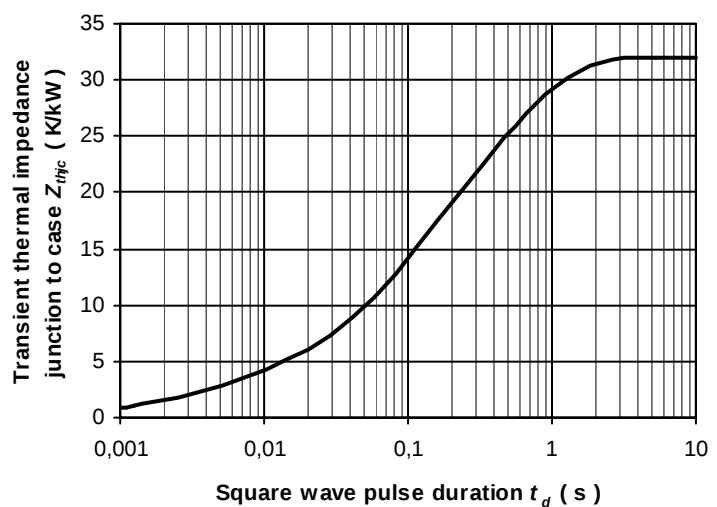


Fig. 2 Dependence transient thermal impedance junction to case on square pulse

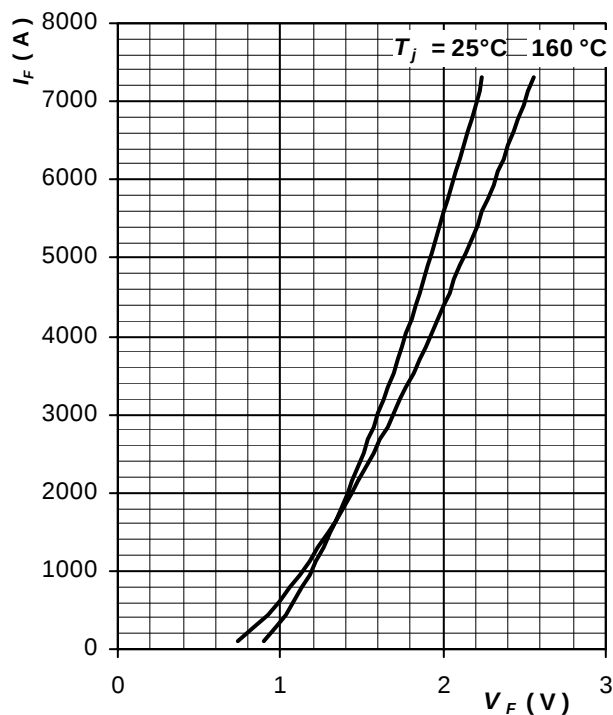


Fig. 3 Maximum forward voltage drop characteristics

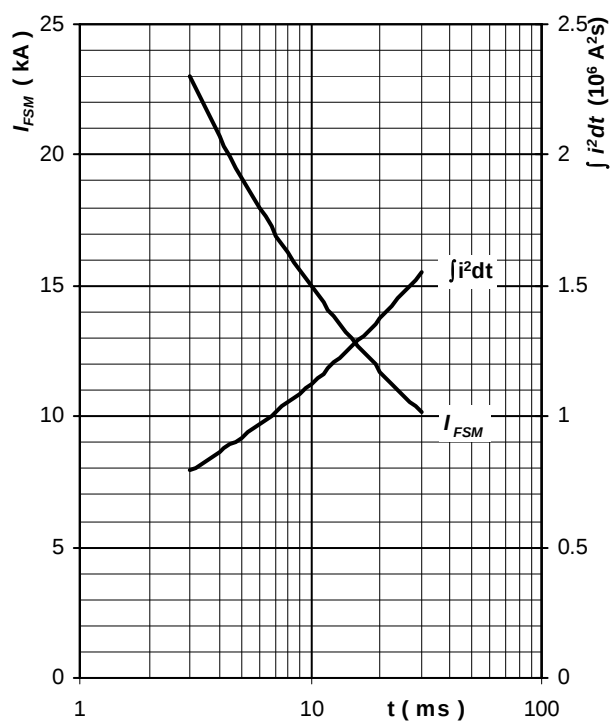


Fig. 4 Surge forward current vs. pulse length, half sine wave, single pulse, $T_j = T_{jmax}$

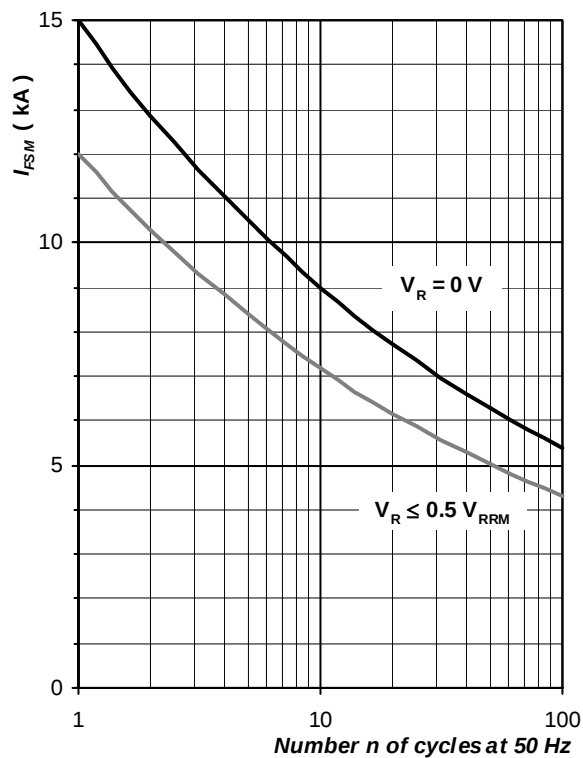


Fig. 5 Surge forward current vs. number of pulses, half sine wave, $T_j = T_{jmax}$

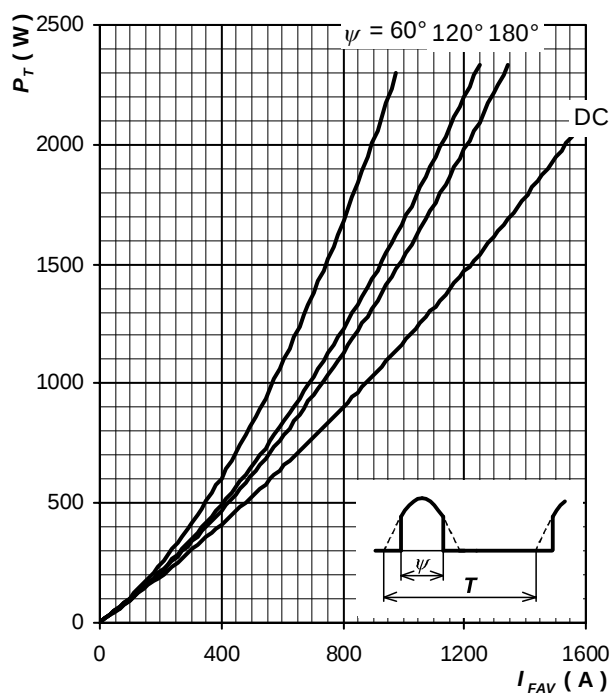


Fig. 6 Forward power loss vs. average forward current, sine waveform, $f = 50$ Hz, $T = 1/f$

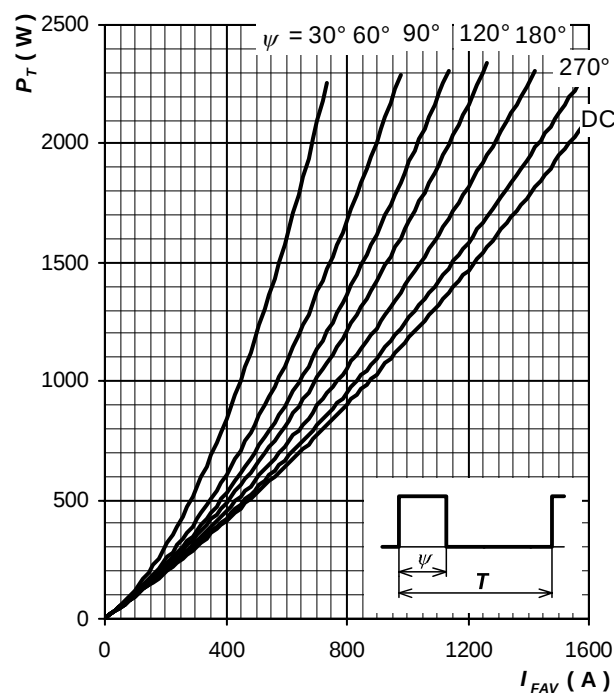


Fig. 7 Forward power loss vs. average forward current, square waveform, $f = 50$ Hz, $T = 1/f$

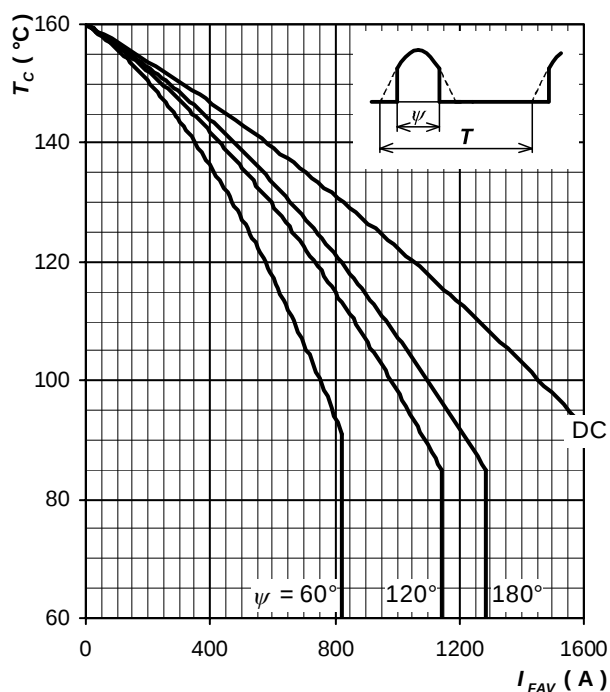


Fig. 8 Max. case temperature vs. aver. forward current, sine waveform, $f = 50$ Hz, $T = 1/f$

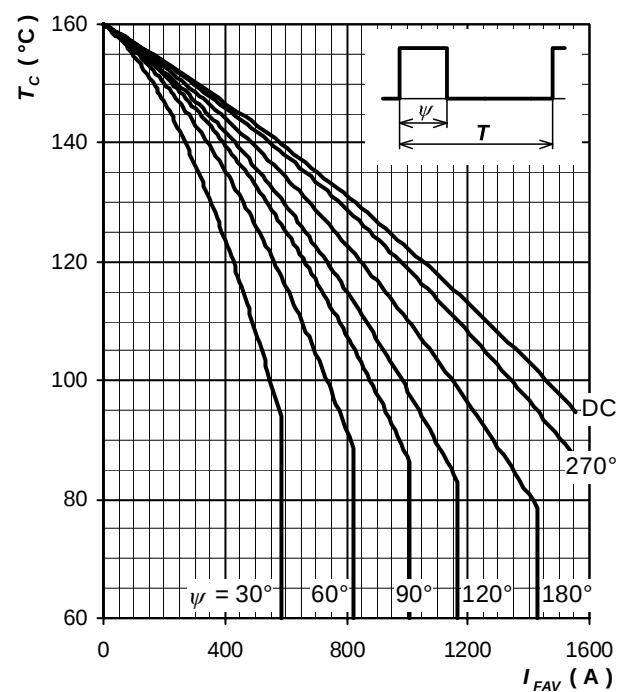


Fig. 9 Max. case temperature vs. aver. forward current, square waveform, $f = 50$ Hz, $T = 1/f$

Notes:

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